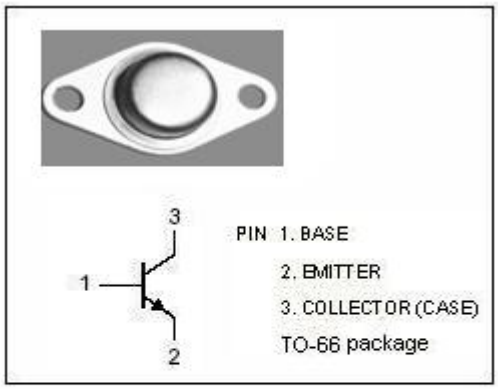
isc Silicon PNP Power Transistors 2SB503

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -50V(Min)
- High Power Dissipation-
  : P_C= 25W(Max)@T_C=25℃
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

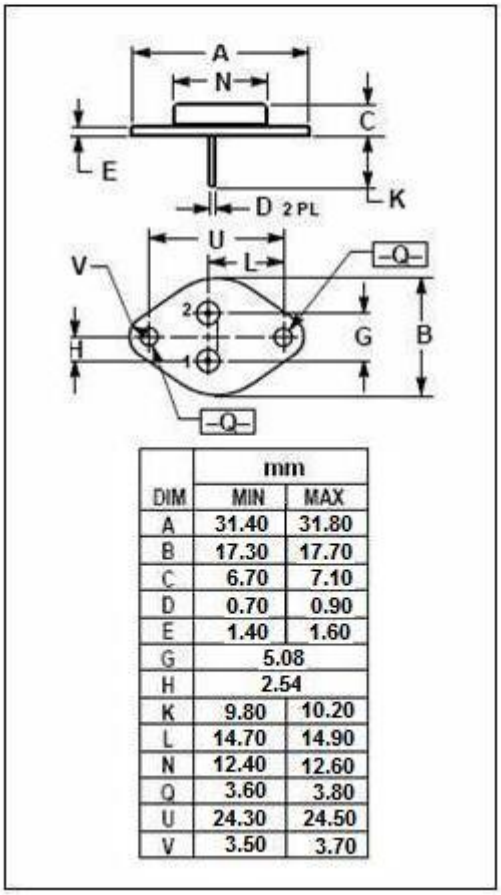


APPLICATIONS

- Designed for audio power amplifier and regulator applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-70	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_C	Collector Current-Continuous	-3	A
P_C	Collector Power Dissipation @T_a=25℃	1.5	W
	Collector Power Dissipation @T_C=25℃	25	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~150	℃



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -30mA; I_B= 0	-50			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -0.1mA; I_E= 0	-70			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA; I_C= 0	-8			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -0.3A			-1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -3A; I_B= -0.3A			-1.8	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -50V; I_E= 0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -8V; I_C= 0			-100	μA
h_{FE-1}	DC Current Gain	I_C= -0.5A; V_{CE}= -5V	30		280	
h_{FE-2}	DC Current Gain	I_C= -2.5A; V_{CE}= -5V	15			

◆ **h_{FE} Classifications**

R	O	Y
30-70	50-140	100-280